

Title (en)

METHOD FOR PRODUCING HIGHLY DOPED SEMICONDUCTOR COMPONENTS

Title (de)

VERFAHREN ZUR HERSTELLUNG HOCHDOTIERTER HALBLEITERBAUELEMENTE

Title (fr)

PROCEDE DE PRODUCTION DE COMPOSANTS SEMI-CONDUCTEURS HAUTEMENT DOPES

Publication

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Application

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Priority

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Abstract (en)

[origin: DE19908400A1] The invention relates to a method for producing semiconductor components. At least one highly doped area is introduced into a wafer. A solid glass layer (2; 4; 2, 3; 4, 5) which is provided with a doping agent is mounted on at least one of the two sides of a semiconductor wafer (1). In a further step, the wafer is heated to high temperatures in such a way that the doping agent leaves the glass layer and penetrates deep into the wafer in order to produce the at least one doped area (10; 11). In a further step, the glass layer is removed. The inventive method is used for producing homogeneous, highly doped areas. Said areas can be introduced through the two sides of the wafer and can have different doping types.

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